

EAST [default.wsp 1]

☐ Drafts
☒ Pending
☒ Active
☐ Failed

L1: (66118) (via plug) and
 L2: (1085) 1 and damascene
 L3: (855) 2 and copper
 L4: (76) 3 and (copper adj oxide)

3 and (copper adj oxide)

	U	D	Document ID	Issue Date	Pages	Title	Current OP	Current XRef
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6309970 B1	20011030	10	Method of forming multi-level copper	438/687	438/618; 438/622;
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6261952 B1	20010717	8	Method of forming copper interconnects with reduced	438/687	438/625; 438/627;
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6211084 B1	20010403	7	Method of forming reliable copper interconnects	438/687	438/626; 438/630;
4	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6165956 A	20001226	8	Methods and apparatus for cleaning semiconductor	510/175	134/2; 134/3;
5	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6165894 A	20001226	7	Method of reliably capping copper interconnects	438/627	438/628; 438/629;
6	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6162301 A	20001219	9	Methods and apparatus for cleaning semiconductor	134/3	134/2; 438/690;
7	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6153523 A	20001128	8	Method of forming high density capping layers for	438/687	438/627; 438/628;
8	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6150269 A	20001121	7	Copper interconnect patterning	438/687	257/762; 438/638;
9	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6147000 A	20001114	11	Method for forming low dielectric passivation of	438/687	438/626; 438/629;
10	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6146988 A	20001114	7	Method of making a semiconductor device	438/618	438/633; 438/788;
11	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6066560 A	20000523	7	Non-linear circuit elements on integrated circuits	438/687	438/627; 438/639;

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	U	#1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6172421 B1	20010109	8	Semiconductor device having an intermetallic layer on	257/751	257/647 ; 257/750	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6153523 A	20001128	8	Method of forming high density capping layers for	438/687	438/627 ; 438/628	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6150269 A	20001121	7	Copper interconnect patterning	438/687	257/762 ; 438/638	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6147000 A	20001114	10	Method for forming low dielectric passivation of	438/687	438/626 ; 438/629	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6114238 A	20000905	5	Self-aligned metal nitride for copper passivation	438/648	438/659 ; 438/687	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6046108 A	20000404	9	Method for selective growth of Cu.sub.3 Ge or Cu.sub.5	438/687	438/626 ; 438/627	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6037257 A	20000314	10	Sputter deposition and annealing of copper alloy	438/687	257/762 ; 257/765	

Failed.

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	U	L	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	P
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6261953 B1	20010717	19	Method of forming a copper oxide film to etch a copper	438/687	427/419.2 ; 438/627	F
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6228767 B1	20010508	7	Non-linear circuit elements on integrated circuits	438/687	257/762 ; 438/627	F